





140V PNP MEDIUM POWER LOW SATURATION TRANSISTOR IN SOT223

Features

- BV_{CEO} > -140V
- I_C = -4A High Continuous Collector Current
- I_{CM} = -10A Peak Pulse Current
- Low Saturation Voltage $V_{CE(sat)} < -120 \text{mV} @ I_C = -1 \text{A}$
- R_{SAT} = 92mΩ for a Low Equivalent On-Resistance
- h_{FE} Specified up to -10A for a High Gain Hold-Up
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

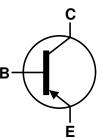
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.112 grams (Approximate)

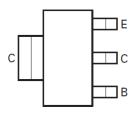




Top View



Device Symbol



Top View Pin-Out

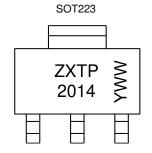
Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP2014GTA	AEC-Q101	ZXTP2014	7	12	1,000
ZXTP2014GTC	AEC-Q101	ZXTP2014	13	12	4,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZXTP 2014 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)



ZXTP2014G

Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-180	V
Collector-Emitter Voltage	$V_{\sf CEO}$	-140	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	Ic	-4	Α
Peak Pulse Current	I _{CM}	-10	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.0		
Power Dissipation	(Note 6)	- P _D -	2.0	W	
Power Dissipation	(Note 7)		1.6	VV	
	(Note 8)		1.2	1	
	(Note 5)		41.7		
Thermal Resistance, Junction to Ambient	(Note 6)	D	62.5		
Thermal nesistance, building to Ambient	(Note 7)	$R_{ heta JA}$	78.1	°C/W	
	(Note 8)		104		
Thermal Resistance Junction to Lead	(Note 9)	$R_{ hetaJL}$	10.5		
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C		

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	8,000	٧	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

 Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.

 Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.

 Same as Note 5, except the device is mounted on minimum recommended pad layout.

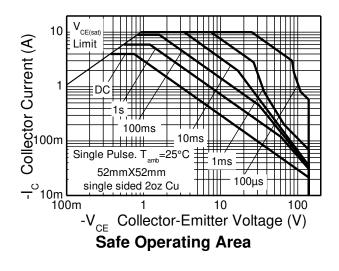
 Thermal resistance from junction to solder-point (at the end of the collector lead).

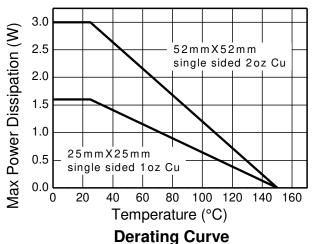
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

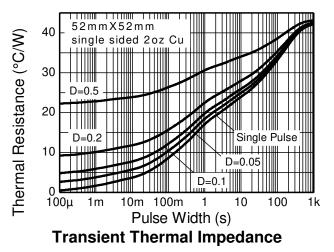


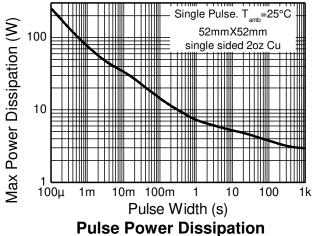
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Thermal Characteristics and Derating Information











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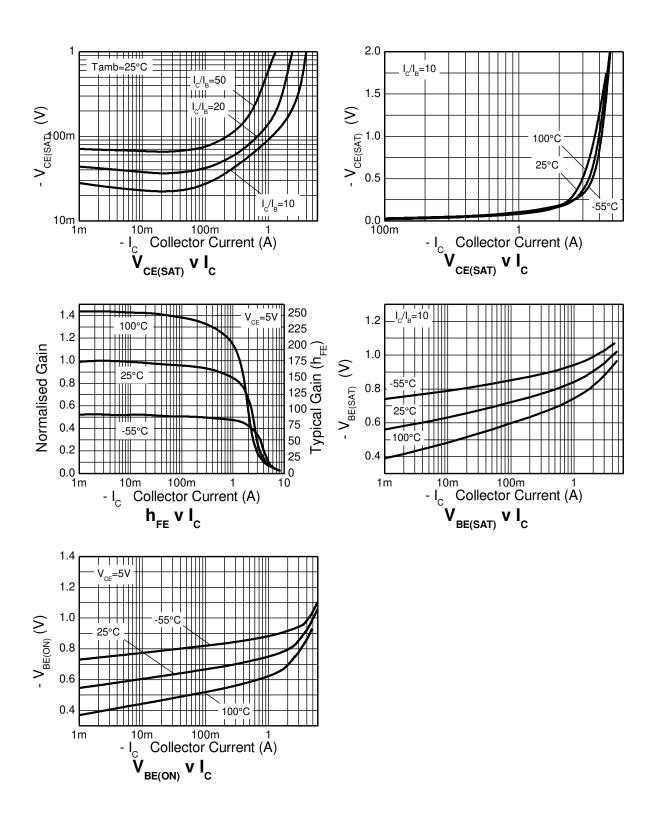
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_CBO	-180	-200	-	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CER}	-180	-200	-	V	$I_C = -1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-140	-160	-	V	$I_C = -1mA$
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	-8.3	-	V	$I_E = -100 \mu A$
Collector Cut-Off Current	I _{CBO}	-	< -1 -	-20 -500	nA nA	V _{CB} = -150V V _{CB} = -150V, T _A = +100°C
Collector Cut-Off Current	l _{CER} R≤1kΩ	-	< -1 -	-20 -500	nA nA	V _{CB} = -150V V _{CB} = -150V, T _A = +100°C
Emitter Cut-Off Current	I _{EBO}	-	< -1	-10	nA	V _{EB} = -6V
	h _{FE}	100	225	-	-	$I_C = -10 \text{mA}, V_{CE} = -5 \text{V}$
DC Current Transfer Static Datic (Note 11)		100	200	300		$I_C = -1A$, $V_{CE} = -5V$
DC Current Transfer Static Ratio (Note 11)		45	100	-		$I_C = -3A, V_{CE} = -5V$
		-	5	-		$I_C = -10A$, $V_{CE} = -5V$
		-	-40	-60	mV	$I_C = -100 \text{mA}, I_B = -5 \text{mA}$
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}	-	-55	-80		$I_C = -0.5A$, $I_B = -50mA$
Collector-Emiller Saturation Voltage (Note 11)		-	-85	-120		$I_C = -1A, I_B = -100mA$
		-	-275	-360		$I_C = -3A$, $I_B = -300mA$
Base-Emitter Saturation Voltage (Note 11)	$V_{BE(sat)}$	-	-940	-1,040	mV	$I_C = -3A$, $I_B = -300mA$
Base-Emitter Turn-On Voltage (Note 11)	$V_{BE(on)}$	-	-830	-930	mV	$I_C = -3A$, $V_{CE} = -5V$
Transitional Frequency	f _T	-	120	-	MHz	$I_{C} = -100 \text{mA}, V_{CE} = -10 \text{V},$ f = 50 MHz
Output Capacitance	C_obo	-	33	-	pF	$V_{CB} = -10V$, $f = 1MHz$
Switching Time	ton	-	42	-	ns	$V_{CC} = -50V, I_{C} = -1A,$
Owitering Time	t _{OFF}	-	636	-	119	$I_{B1} = -I_{B2} = -100 \text{mA}$

Note: 11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



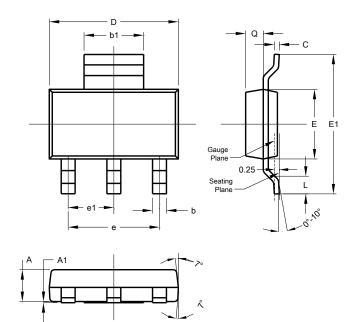
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)





Package Outline Dimensions

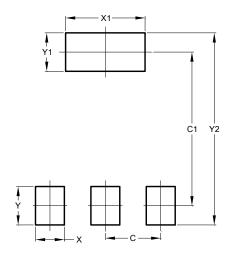
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Υ	1.60		
Y1	1.60		
Y2	8.00		

For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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